Implementation of a Dual on Die 140 V Super-Junction Power Transistors

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Abstract

Increasing the switching frequency for switch mode power supplies is one method to achieve smaller, lighter weight and hopefully cheaper power converters.

Silicon is not only the dominant material used to produce the switches but also it allows more circuitry to be easily integrated on the same die.

This work presents an application customized switches to be used in switch mode power supplies.

The prototype chip was implemented using a 0.18 μ m SOI process and includes dual electrically isolated 140 V, 1.2 Ω N-channel MOSFETs.

Project Objectives

Wider Objective:

Develop an Integrated switch-mode power supplies utilize few external components.

Specific Objectives:

To integrate the DTU Elektro proven dc-dc converter topologies in a single module / chip.

To develop state of the art, high power density, high quality power supply prototypes.





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Semiconductor Technology

First Generation Switches

- Dual on Die" Electrically 140 V Isolated Super-Junction N-Channel Transistors.
- Using a 0.18 μm SOI process.
- Ron = 1.2Ω for each switch. (@ 0.1 Vds)
- Designed for homogenous current distribution across the die.
- Die Size is 1.6 mm x 1.6 mm



Photomicrograph of the designed chip



Characterization PCBs



Characterization Results